

# MOSFET – Single P-Channel POWERTRENCH®

## 2.5 V Specified

## FDN336P

### Description

This P-Channel 2.5 V specified MOSFET is produced using onsemi's advanced POWERTRENCH process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

These devices are well suited for portable electronics applications: load switching and power management, battery charging circuits and DC-DC conversion.

### Features

- -1.3 A, -20 V
  - ♦  $R_{DS(on)} = 0.20 \Omega @ V_{GS} = -4.5 V$
  - ♦  $R_{DS(on)} = 0.27 \Omega @ V_{GS} = -2.5 V$
- Low Gate Charge (3.6 nC Typical)
- High Performance Trench Technology for Extremely Low  $R_{DS(ON)}$
- SUPERSOT™ -3 Provides Low  $R_{DS(ON)}$  and 30% Higher Power Handling Capability than SOT23 in the Same Footprint

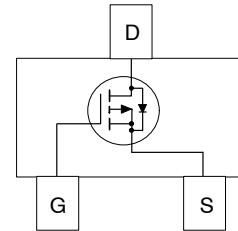
### ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Value	Unit
$V_{DSS}$	Drain to Source Voltage	-20	V
$V_{GSS}$	Gate to Source Voltage	$\pm 8$	V
$I_D$	Drain Current - Continuous (Note 1a) - Pulsed	-1.3 -10	A
$P_D$	Maximum Power Dissipation (Note 1a) (Note 1b)	0.5 0.46	W
$T_J, T_{stg}$	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ C$

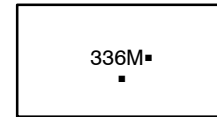
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



SOT-23  
 CASE 527AG



### MARKING DIAGRAM



- 336 = Specific Device Code
- M = Month Code
- = Pb-Free Package

### ORDERING INFORMATION

Device	Package	Shipping†
FDN336P	SOT-23 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

# FDN336P

## THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	250	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	75	°C/W

## ELECTRICAL CHARACTERISTICS $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
$BV_{DSS}$	Drain to Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-20	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$	-	-16	-	mV/°C
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = -16\text{ V}, V_{GS} = 0\text{ V}$	-	-	-1	$\mu\text{A}$
		$V_{DS} = -16\text{ V}, V_{GS} = 0\text{ V}, T_J = 55^\circ\text{C}$	-	-	-10	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage Forward	$V_{GS} = 8\text{ V}, V_{DS} = 0\text{ V}$	-	-	100	nA
$I_{GSSR}$	Gate-Body Leakage Reverse	$V_{GS} = -8\text{ V}, V_{DS} = 0\text{ V}$	-	-	-100	nA

### On Characteristics (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-0.4	-0.9	-1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$	-	3	-	mV/°C
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = -4.5\text{ V}, I_D = -1.3\text{ A}$	-	0.122	0.2	$\Omega$
		$V_{GS} = -4.5\text{ V}, I_D = -1.3\text{ A}, T_J = 125^\circ\text{C}$	-	0.18	0.32	
		$V_{GS} = -2.5\text{ V}, I_D = -1.1\text{ A}$	-	0.19	0.27	
$I_{D(on)}$	On-State Drain Current	$V_{GS} = -4.5\text{ V}, V_{DS} = -5\text{ V}$	-5	-	-	A
$g_{FS}$	Forward Transconductance	$V_{DS} = -4.5\text{ V}, I_D = -2\text{ A}$	-	4	-	S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}$	-	330	-	pF
$C_{oss}$	Output Capacitance		-	80	-	pF
$C_{rss}$	Reverse Transfer Capacitance		-	35	-	pF

### Switching Characteristics (Note 2)

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -5\text{ V}, I_D = -0.5\text{ A},$ $V_{GS} = -4.5\text{ V}, R_{GEN} = 6\ \Omega$	-	7	15	ns
$t_r$	Turn-On Rise Time		-	12	22	ns
$t_{d(off)}$	Turn-Off Delay Time		-	16	26	ns
$t_f$	Turn-Off Fall Time		-	5	12	ns
$Q_g$	Total Gate Change	$V_{DS} = -10\text{ V}, I_D = -2\text{ A},$ $V_{GS} = -4.5\text{ V}$	-	3.6	5	nC
$Q_{gs}$	Gate-Source Change		-	0.8	-	nC
$Q_{gd}$	Gate-Drain Change		-	0.7	-	nC

### Drain-Source Diode Characteristics and Maximum Ratings

$I_S$	Maximum Continuous Drain-Source Diode Forward Current	-	-	-0.42	A	
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = -0.42\text{ A}$ (Note 2)	-	-0.7	-1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

#### NOTES:

- $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a)  $250^\circ\text{C/W}$  when mounted on a 0.02 in<sup>2</sup> Pad of 2 oz. Cu.



b)  $270^\circ\text{C/W}$  on a minimum mounting pad of 2 oz. Cu.

Scale 1 : 1 on letter size paper

- Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

TYPICAL CHARACTERISTICS

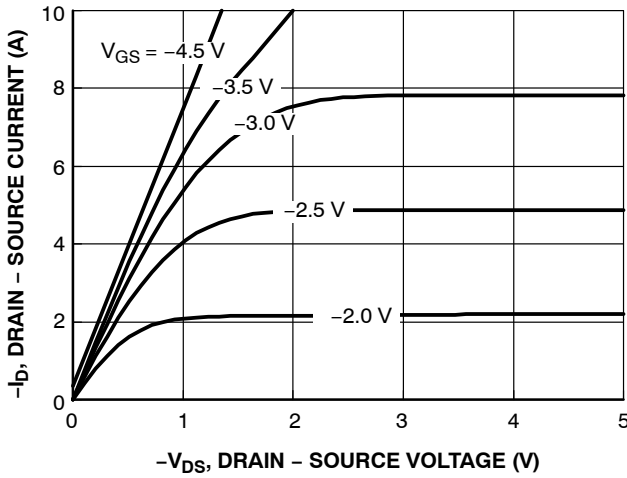


Figure 1. On-Region Characteristics

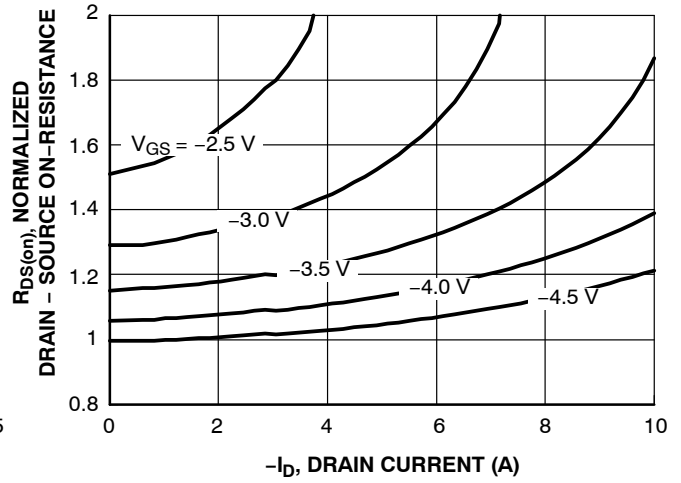


Figure 2. On-Resistance Variation with Drain Current and Gate

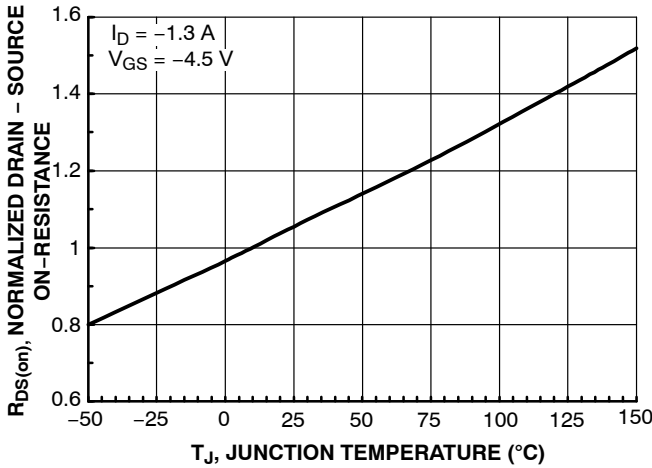


Figure 3. On-Resistance Variation with Temperature

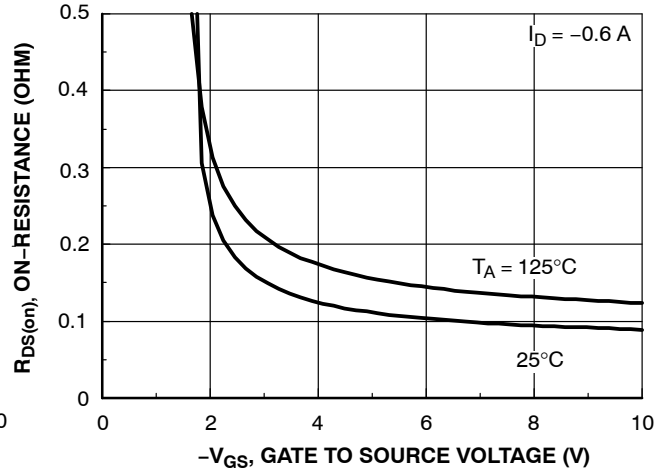


Figure 4. On-Resistance Variation with Gate-to-Source Voltage

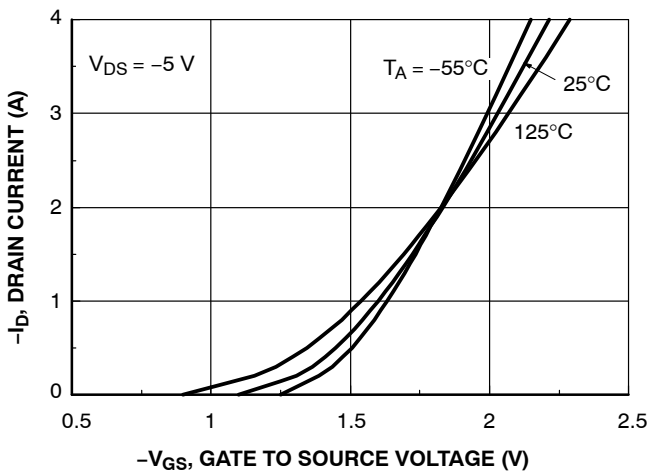


Figure 5. Transfer Characteristics

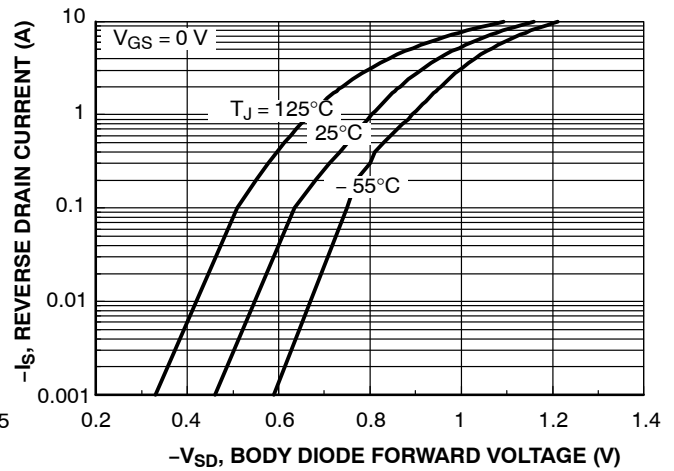


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

TYPICAL CHARACTERISTICS (CONTINUED)

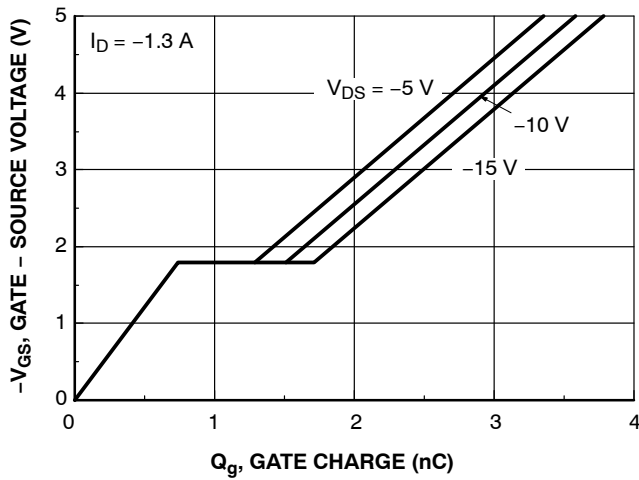


Figure 7. Gate Charge Characteristics

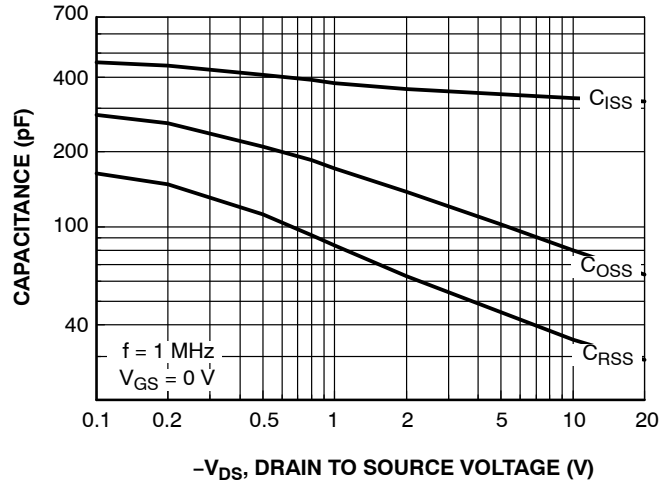


Figure 8. Capacitance Characteristics

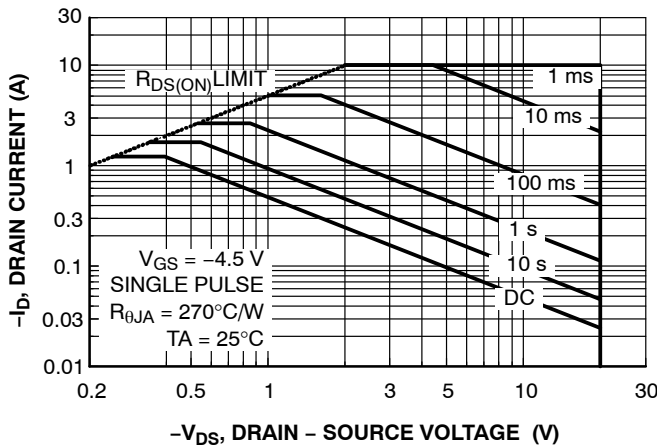


Figure 9. Maximum Safe Operating Area

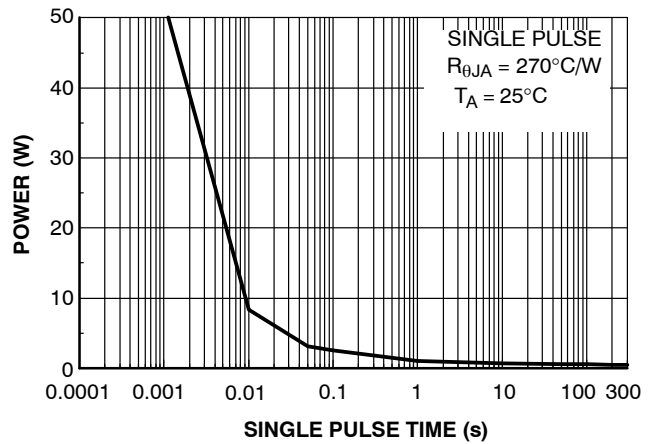


Figure 10. Single Pulse Maximum Power Dissipation

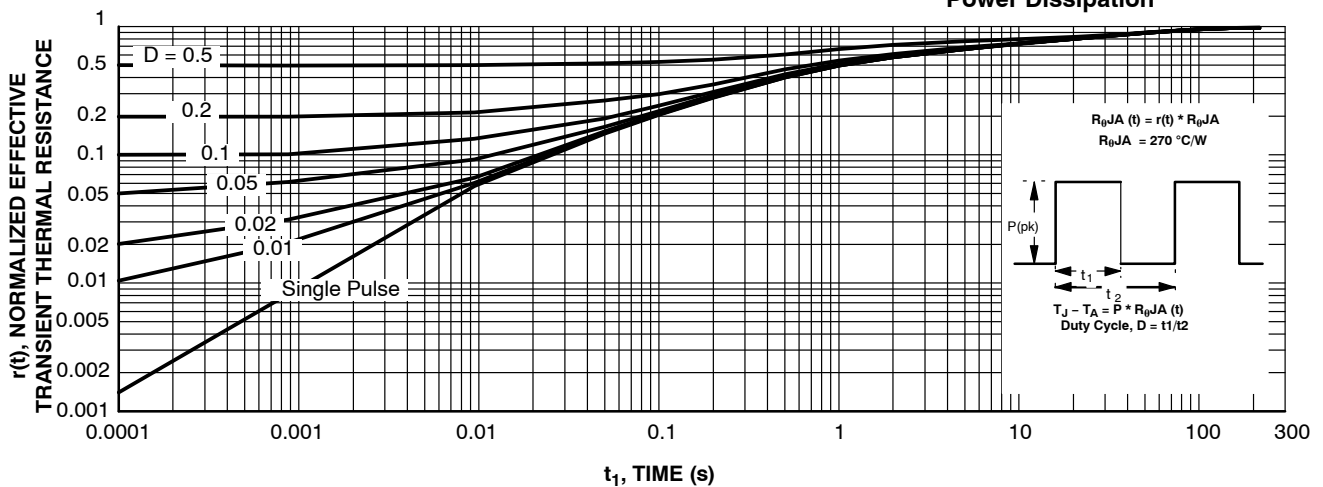


Figure 11. Transient Thermal Response Curve

Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

ON Semiconductor®



### SOT-23/SUPERSOT™ -23, 3 LEAD, 1.4x2.9

CASE 527AG  
ISSUE A

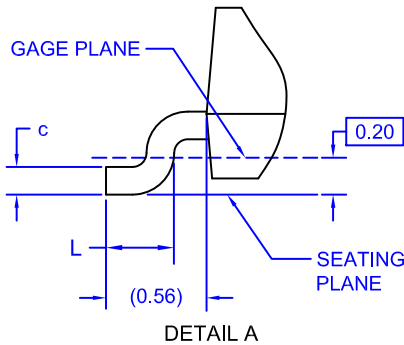
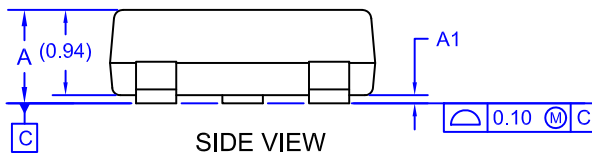
DATE 09 DEC 2019



NOTES: UNLESS OTHERWISE SPECIFIED

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. ALL DIMENSIONS ARE IN MILLIMETERS.
3. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.

DIM	MIN.	NOM.	MAX.
A	0.85	0.95	1.12
A1	0.00	0.05	0.10
b	0.370	0.435	0.508
c	0.085	0.150	0.180
D	2.80	2.92	3.04
E	2.31	2.51	2.71
E1	1.20	1.40	1.52
e	0.95 BSC		
e1	1.90 BSC		
L	0.33	0.38	0.43



\*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

#### GENERIC MARKING DIAGRAM\*



- XXX = Specific Device Code
- M = Month Code
- = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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